

RF Power Field Effect Transistors

N-Channel Enhancement-Mode Lateral MOSFETs

Designed for broadband commercial and industrial applications with frequencies from 865 to 895 MHz. The high gain and broadband performance of these devices make them ideal for large-signal, common-source amplifier applications in 26 volt base station equipment.

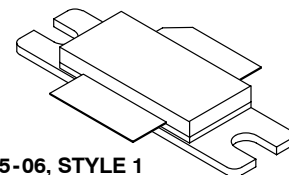
- Typical CDMA Performance @ 880 MHz, 26 Volts, $I_{DQ} = 700$ mA
IS-95 CDMA Pilot, Sync, Paging, Traffic Codes 8 Through 13
Output Power — 20 Watts
Power Gain — 17.9 dB
Efficiency — 28%
Adjacent Channel Power —
750 kHz: -45.0 dBc @ 30 kHz BW
1.98 MHz: -60.0 dBc @ 30 kHz BW
- Capable of Handling 10:1 VSWR, @ 26 Vdc, 880 MHz, 90 Watts CW Output Power

Features

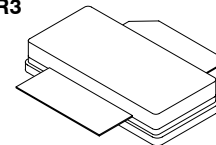
- Internally Matched for Ease of Use
- High Gain, High Efficiency and High Linearity
- Integrated ESD Protection
- Designed for Maximum Gain and Insertion Phase Flatness
- Excellent Thermal Stability
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Low Gold Plating Thickness on Leads, 40 μ ” Nominal.
- RoHS Compliant
- In Tape and Reel. R3 Suffix = 250 Units per 56 mm, 13 inch Reel.

MRF9085LR3
MRF9085LSR3

880 MHz, 90 W, 26 V
LATERAL N-CHANNEL
RF POWER MOSFETs



CASE 465-06, STYLE 1
NI-780
MRF9085LR3



CASE 465A-06, STYLE 1
NI-780S
MRF9085LSR3

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Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	- 0.5, +65	Vdc
Gate-Source Voltage	V_{GS}	- 0.5, +15	Vdc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25 $^\circ\text{C}$	P_D	250 1.43	W W/ $^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to +150	$^\circ\text{C}$
Case Operating Temperature	T_C	150	$^\circ\text{C}$
Operating Junction Temperature	T_J	200	$^\circ\text{C}$

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.7	$^\circ\text{C}/\text{W}$

Table 3. ESD Protection Characteristics

Test Conditions	Class
Human Body Model	1 (Minimum)
Machine Model MRF9085LR3 MRF9085LSR3	M2 (Minimum) M1 (Minimum)

Table 4. Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Off Characteristics					
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 65\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	10	μAdc
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 26\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	1	μAdc
Gate-Source Leakage Current ($V_{GS} = 5\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	—	—	1	μAdc
On Characteristics					
Gate Threshold Voltage ($V_{DS} = 10\text{ Vdc}$, $I_D = 300\ \mu\text{Adc}$)	$V_{GS(th)}$	2.0	—	4.0	Vdc
Gate Quiescent Voltage ($V_{DS} = 26\text{ Vdc}$, $I_D = 700\ \text{mAdc}$)	$V_{GS(Q)}$	—	3.7	—	Vdc
Drain-Source On-Voltage ($V_{GS} = 10\text{ Vdc}$, $I_D = 2\ \text{Adc}$)	$V_{DS(on)}$	—	0.19	0.4	Vdc
Forward Transconductance ($V_{DS} = 10\text{ Vdc}$, $I_D = 6\ \text{Adc}$)	g_{fs}	—	8.0	—	S
Dynamic Characteristics ⁽¹⁾					
Output Capacitance ($V_{DS} = 26\text{ Vdc} \pm 30\ \text{mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{oss}	—	73	—	pF
Reverse Transfer Capacitance ($V_{DS} = 26\text{ Vdc} \pm 30\ \text{mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{rss}	—	2.9	—	pF

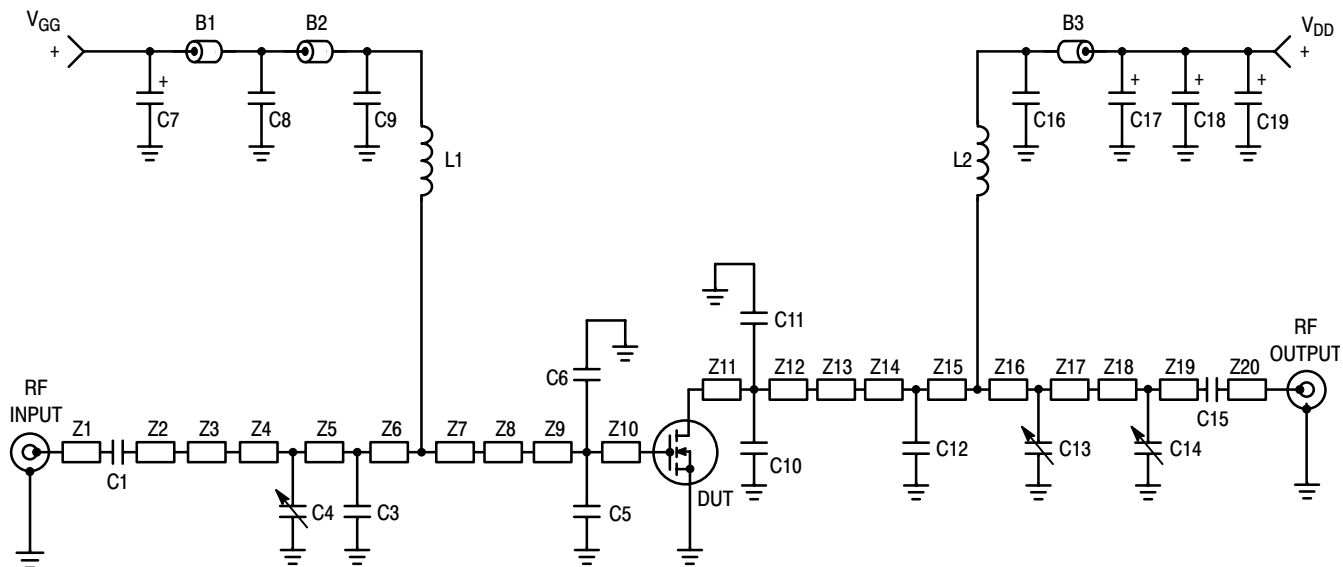
1. Part is internally input matched.

(continued)

Table 4. Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted) (continued)

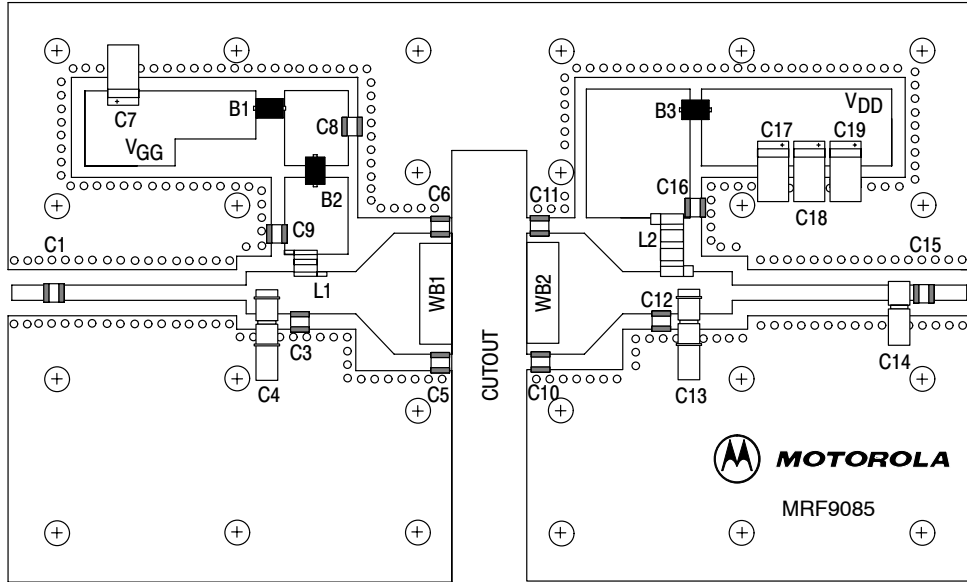
Characteristic	Symbol	Min	Typ	Max	Unit
Functional Tests (In Freescale Test Fixture, 50 ohm system)					
Two-Tone Common-Source Amplifier Power Gain ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 90\text{ W PEP}$, $I_{DQ} = 700\text{ mA}$, $f_1 = 880.0\text{ MHz}$, $f_2 = 880.1\text{ MHz}$)	G_{ps}	17	17.9	—	dB
Two-Tone Drain Efficiency ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 90\text{ W PEP}$, $I_{DQ} = 700\text{ mA}$, $f_1 = 880.0\text{ MHz}$, $f_2 = 880.1\text{ MHz}$)	η	36	40	—	%
3rd Order Intermodulation Distortion ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 90\text{ W PEP}$, $I_{DQ} = 700\text{ mA}$, $f_1 = 880.0\text{ MHz}$, $f_2 = 880.1\text{ MHz}$)	IMD	—	-31	-28	dBc
Input Return Loss ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 90\text{ W PEP}$, $I_{DQ} = 700\text{ mA}$, $f_1 = 880.0\text{ MHz}$, $f_2 = 880.1\text{ MHz}$)	IRL	—	-21	-9	dB
Two-Tone Common-Source Amplifier Power Gain ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 90\text{ W PEP}$, $I_{DQ} = 700\text{ mA}$, $f_1 = 865.0\text{ MHz}$, $f_2 = 865.1\text{ MHz}$)	G_{ps}	—	17.9	—	dB
Two-Tone Drain Efficiency ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 90\text{ W PEP}$, $I_{DQ} = 700\text{ mA}$, $f_1 = 865.0\text{ MHz}$, $f_2 = 865.1\text{ MHz}$)	η	—	40.0	—	%
3rd Order Intermodulation Distortion ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 90\text{ W PEP}$, $I_{DQ} = 700\text{ mA}$, $f_1 = 865.0\text{ MHz}$, $f_2 = 865.1\text{ MHz}$)	IMD	—	-31	—	dBc
Input Return Loss ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 90\text{ W PEP}$, $I_{DQ} = 700\text{ mA}$, $f_1 = 865.0\text{ MHz}$, $f_2 = 865.1\text{ MHz}$)	IRL	—	-16	—	dB
Power Output, 1 dB Compression Point, CW ($V_{DD} = 26\text{ Vdc}$, $I_{DQ} = 700\text{ mA}$, $f_1 = 880.0\text{ MHz}$)	P_{1dB}	—	105	—	W
Common-Source Amplifier Power Gain ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 90\text{ W CW}$, $I_{DQ} = 700\text{ mA}$, $f_1 = 880.0\text{ MHz}$)	G_{ps}	—	17.5	—	dB
Drain Efficiency ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 90\text{ W CW}$, $I_{DQ} = 700\text{ mA}$, $f_1 = 880.0\text{ MHz}$)	η	—	51	—	%
Power Output, 1 dB Compression Point, CW ⁽¹⁾ ($V_{DD} = 26\text{ Vdc}$, $I_{DQ} = 700\text{ mA}$, $f_1 = 960\text{ MHz}$)	P_{1dB}	—	105	—	W

1. These values are derived from a 960 MHz optimized test fixture. Values are not applicable to Figures 1 and 2.



B1, B2, B3	Short Ferrite Beads, Surface Mount	Z6	0.076" x 0.220" Microstrip
C1, C9, C15, C16	47 pF Chip Capacitors, ATC	Z7	0.261" x 0.220" Microstrip
C3	5.6 pF Chip Capacitor, ATC	Z8	0.220" x 0.630" x 0.200" Taper
C4, C13	0.8 - 8.0 Variable Capacitors, Gigatrim	Z9	0.240" x 0.630" Microstrip
C5, C6, C12	8.2 pF Chip Capacitors, ATC	Z10	0.060" x 0.630" Microstrip
C7, C17, C18, C19	10 μ F, 35 V Tantalum Surface Mount Capacitors, Kemet	Z11	0.067" x 0.630" Microstrip
C8	20 K pF Chip Capacitor, ATC	Z12	0.233" x 0.630" Microstrip
C10, C11	16 pF Chip Capacitors, ATC	Z13	0.630" x 0.220" x 0.200" Taper
C14	0.6 - 4.5 Variable Capacitor, Gigatrim	Z14	0.200" x 0.220" Microstrip
L1	7.15 nH Inductor, Coilcraft	Z15	0.055" x 0.220" Microstrip
L2	17.5 nH Inductor, Coilcraft	Z16	0.088" x 0.220" Microstrip
N1, N2	N-Type Panel Mount, Stripline, M/A-Com	Z17	0.226" x 0.220" Microstrip
WB1, WB2	5 Mil BeCu Shim (0.225 x 0.525)	Z18	0.868" x 0.080" Microstrip
Z1	0.219" x 0.080" Microstrip	Z19	0.129" x 0.080" Microstrip
Z2	0.150" x 0.080" Microstrip	Z20	0.223" x 0.080" Microstrip
Z3	0.851" x 0.080" Microstrip	PCB	Arlon GX-0300-55-22, 30 mils
Z4	0.125" x 0.220" Microstrip		$\epsilon_r = 2.55$
Z5	0.123" x 0.220" Microstrip		

Figure 1. 865-895 MHz Broadband Test Circuit Schematic



Freescale has begun the transition of marking Printed Circuit Boards (PCBs) with the Freescale Semiconductor signature/logo. PCBs may have either Motorola or Freescale markings during the transition period. These changes will have no impact on form, fit or function of the current product.

Figure 2. 865-895 MHz Broadband Test Circuit Component Layout

TYPICAL CHARACTERISTICS

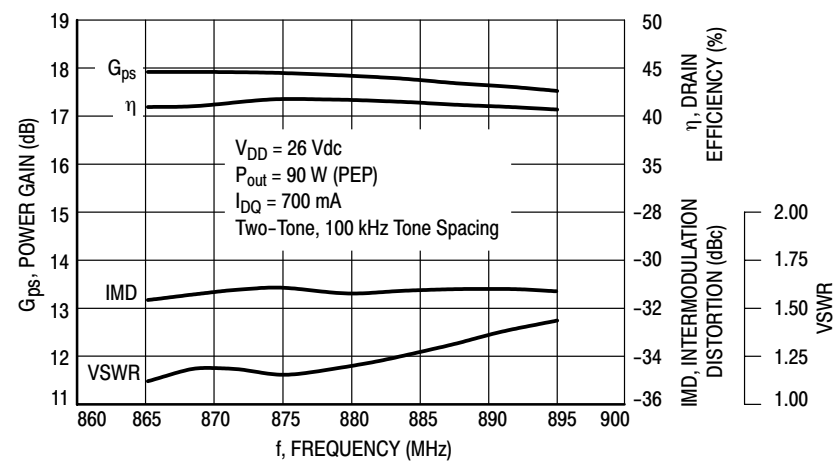


Figure 3. Class AB Broadband Circuit Performance

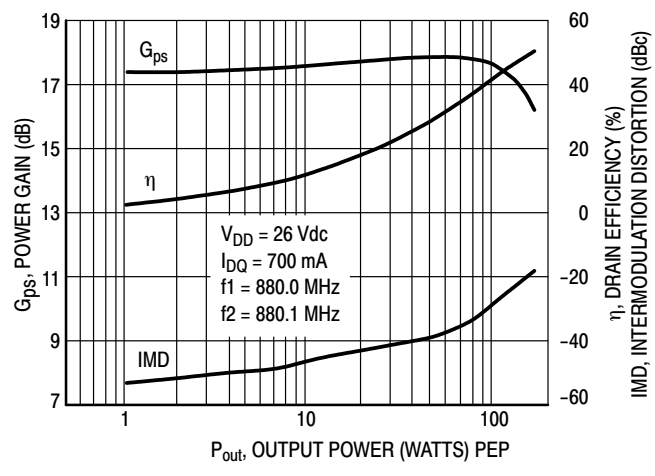


Figure 4. Power Gain, Efficiency, IMD versus Output Power

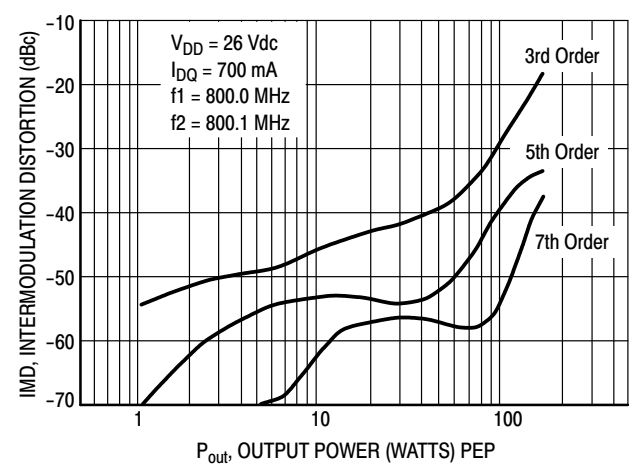


Figure 5. Intermodulation Distortion Products versus Output Power

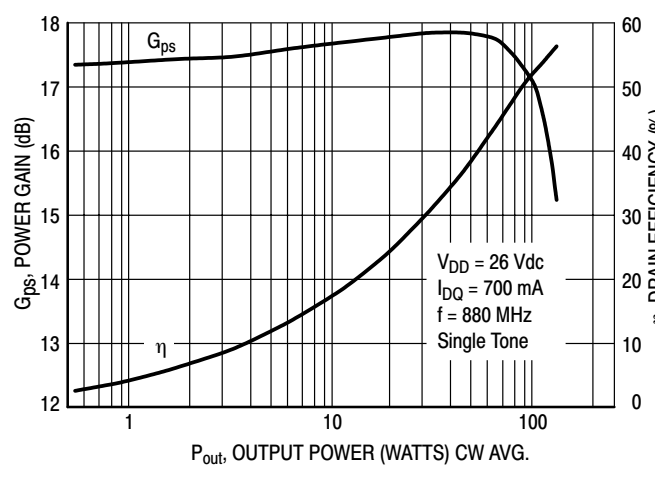


Figure 6. Power Gain, Efficiency versus Output Power

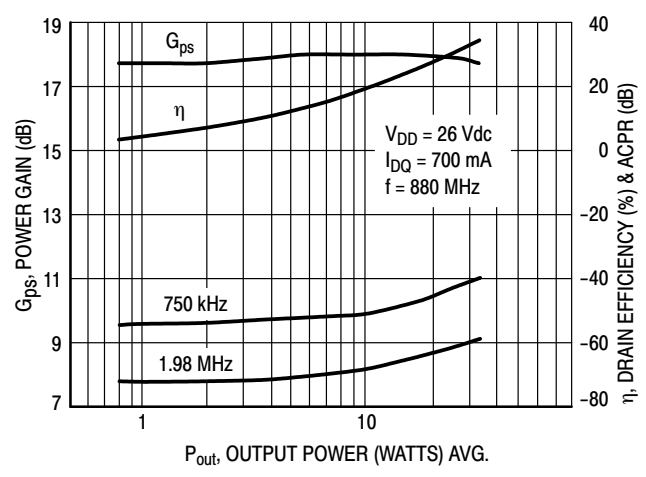
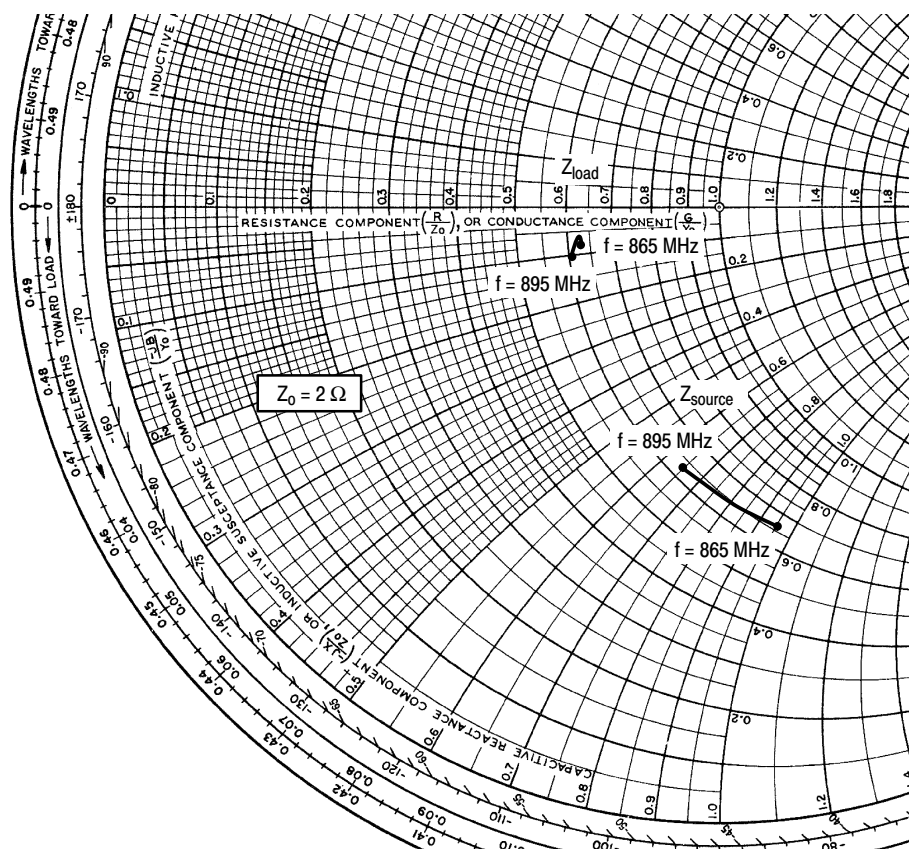


Figure 7. Power Gain, Efficiency, ACPR versus Output Power

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$V_{DD} = 26\text{ V}$, $I_{DQ} = 700\text{ mA}$, $P_{out} = 90\text{ W PEP}$

f MHz	Z_{source} Ω	Z_{load} Ω
865	$1.35 - j1.92$	$1.26 - j0.15$
880	$1.33 - j1.66$	$1.26 - j0.10$
895	$1.28 - j1.30$	$1.21 - j0.20$

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

Note: Z_{load} was chosen based on tradeoffs between gain, output power, drain efficiency and intermodulation distortion.

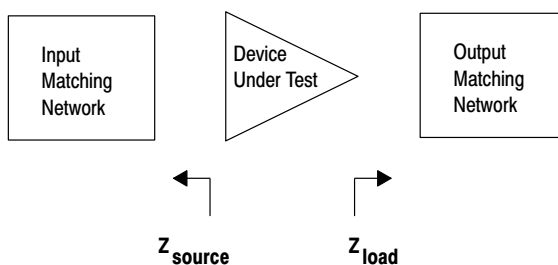


Figure 8. Series Equivalent Source and Load Impedance

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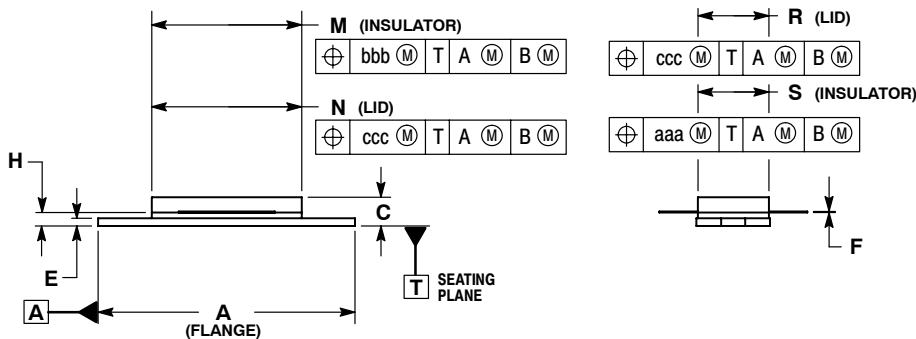
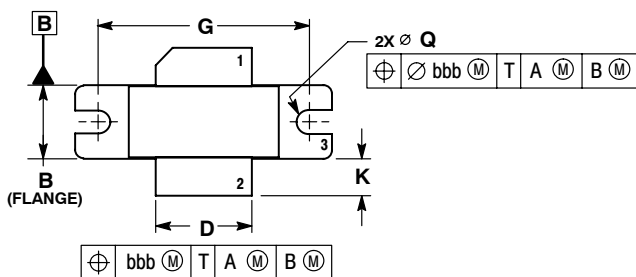
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NOTES

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PACKAGE DIMENSIONS

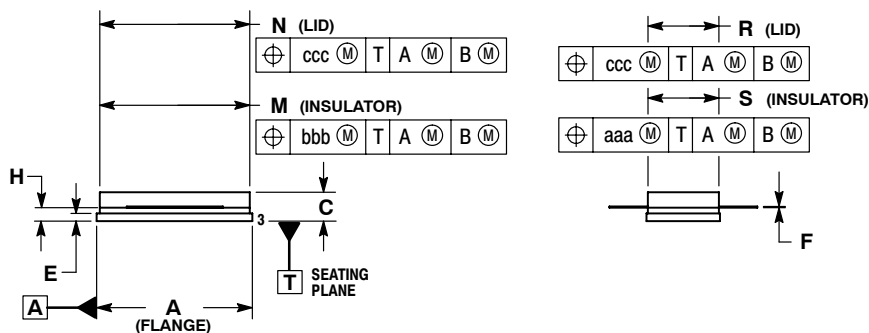
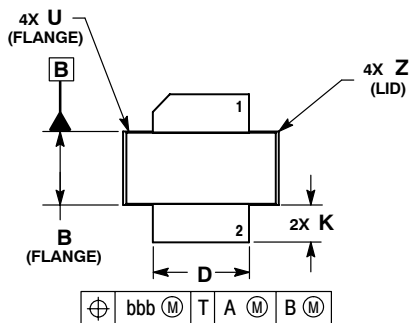


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.
 2. CONTROLLING DIMENSION: INCH.
 3. DELETED
 4. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.335	1.345	33.91	34.16
B	0.380	0.390	9.65	9.91
C	0.125	0.170	3.18	4.32
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
G	1.100 BSC		27.94 BSC	
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.774	0.786	19.66	19.96
N	0.772	0.788	19.60	20.00
Q	Ø.118	Ø.138	Ø.300	Ø.351
R	0.365	0.375	9.27	9.53
S	0.365	0.375	9.27	9.52
aaa	0.005 REF		0.127 REF	
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

- STYLE 1:
 PIN 1. DRAIN
 2. GATE
 3. SOURCE

**CASE 465-06
 ISSUE G
 NI-780
 MRF9085LR3**



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.
 2. CONTROLLING DIMENSION: INCH.
 3. DELETED
 4. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.805	0.815	20.45	20.70
B	0.380	0.390	9.65	9.91
C	0.125	0.170	3.18	4.32
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.774	0.786	19.61	20.02
N	0.772	0.788	19.61	20.02
R	0.365	0.375	9.27	9.53
S	0.365	0.375	9.27	9.52
U	---	0.040	---	1.02
Z	---	0.030	---	0.76
aaa	0.005 REF		0.127 REF	
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

- STYLE 1:
 PIN 1. DRAIN
 2. GATE
 5. SOURCE

**CASE 465A-06
 ISSUE H
 NI-780S
 MRF9085LSR3**

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How to Reach Us:

Home Page:
www.freescale.com

E-mail:
support@freescale.com

USA/Europe or Locations Not Listed:
Freescale Semiconductor
Technical Information Center, CH370
1300 N. Alma School Road
Chandler, Arizona 85224
+1-800-521-6274 or +1-480-768-2130
support@freescale.com

Europe, Middle East, and Africa:
Freescale Halbleiter Deutschland GmbH
Technical Information Center
Schatzbogen 7
81829 Muenchen, Germany
+44 1296 380 456 (English)
+46 8 52200080 (English)
+49 89 92103 559 (German)
+33 1 69 35 48 48 (French)
support@freescale.com

Japan:
Freescale Semiconductor Japan Ltd.
Headquarters
ARCO Tower 15F
1-8-1, Shimo-Meguro, Meguro-ku,
Tokyo 153-0064
Japan
0120 191014 or +81 3 5437 9125
support.japan@freescale.com

Asia/Pacific:
Freescale Semiconductor Hong Kong Ltd.
Technical Information Center
2 Dai King Street
Tai Po Industrial Estate
Tai Po, N.T., Hong Kong
+800 2666 8080
support.asia@freescale.com

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